

## NCE Automotive N-Channel Super Trench Power MOSFET

### Description

The NCEAP40T20AGU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

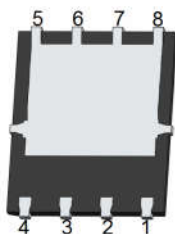
### General Features

- $V_{DS} = 40V, I_D = 300A$  (Silicon Limited)  
 $R_{DS(ON)} = 0.95m\Omega$ , typical @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100%  $\Delta V_{ds}$  tested
- **AEC-Q101 qualified**

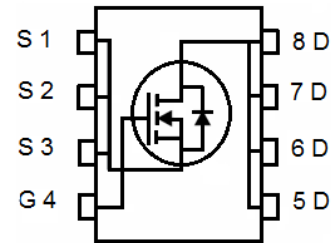
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP40T20AGU	NCEAP40T20AGU	DFN5X6-8L	Ø330mm	12mm	5000units

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous(Silicon Limited) <sup>(Note1)</sup>	$I_D$	300	A
Drain Current-Continuous(Silicon Limited) <sup>(Note1)</sup>	$I_D(100^\circ C)$	213	A
Drain Current-Continuous (Package Limited)	$I_D$	200	A
Pulsed Drain Current	$I_{DM}$	800	A
Maximum Power Dissipation	$P_D$	220	W
Derating factor		1.47	W/°C
Single pulse avalanche energy <sup>(Note 2)</sup>	$E_{AS}$	1800	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.68	°C/W
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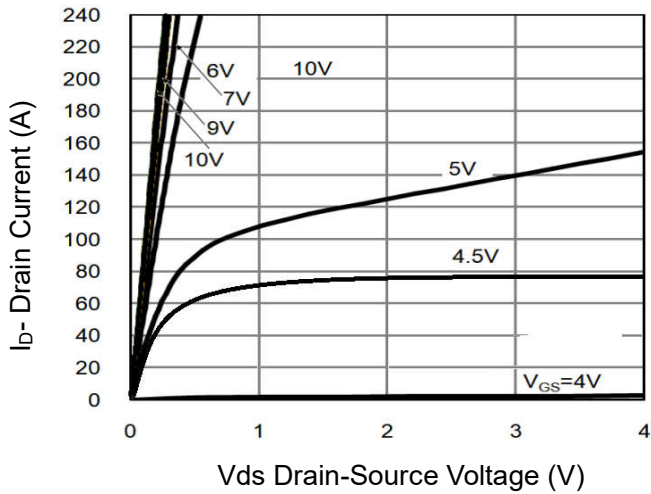
## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	-	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	0.95	1.3	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		90	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	5834.6	-	pF
Output Capacitance	C <sub>oss</sub>		-	2320.5	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	70	-	pF
<b>Switching Characteristics</b> <sup>(Note 1)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	14.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	58	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	91	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	29.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	19	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	300	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	35	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs	-	120	-	nC

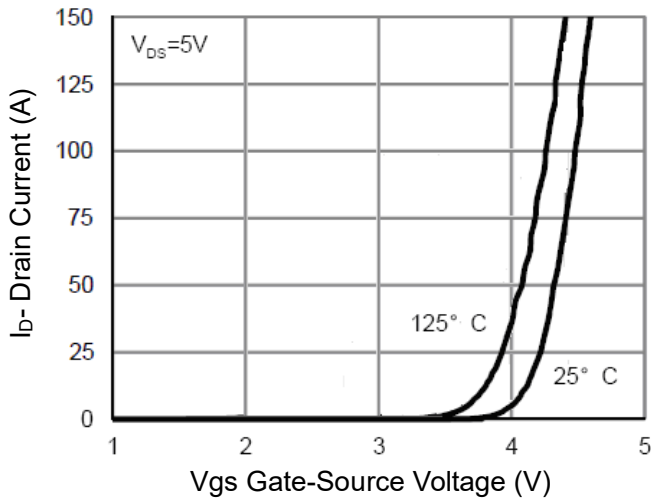
### Notes:

1. Defined by design. Not Subject to production test
2. EAS condition : T<sub>j</sub>=25°C, V<sub>DD</sub>=20V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=175°C. The SOA curve provides a single pulse rating.

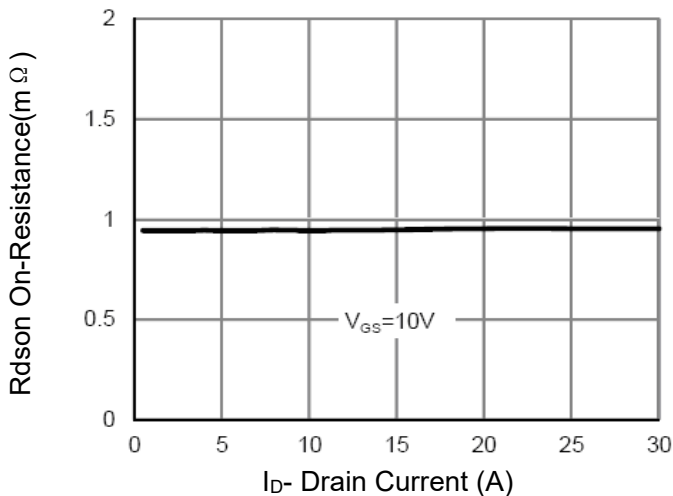
## Typical Electrical and Thermal Characteristics



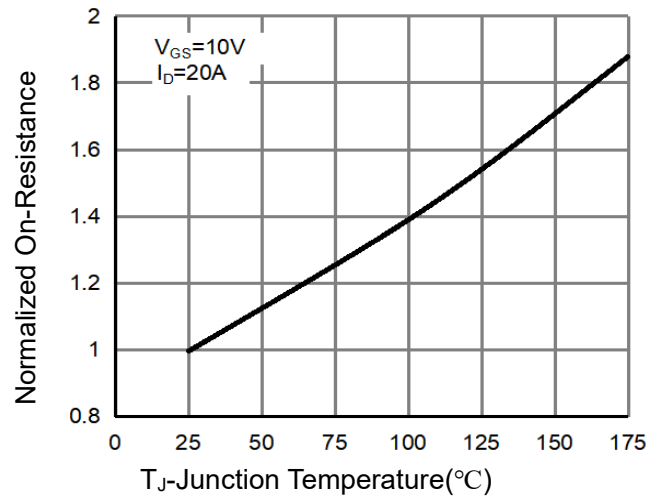
**Figure 1 Output Characteristics**



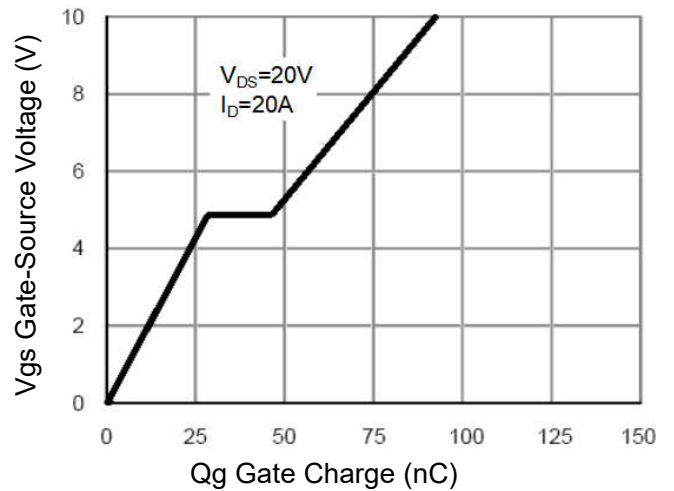
**Figure 2 Transfer Characteristics**



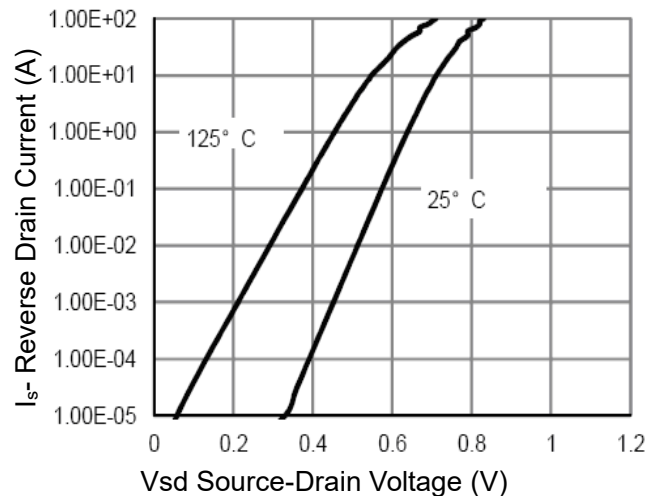
**Figure 3 Rdson- Drain Current**



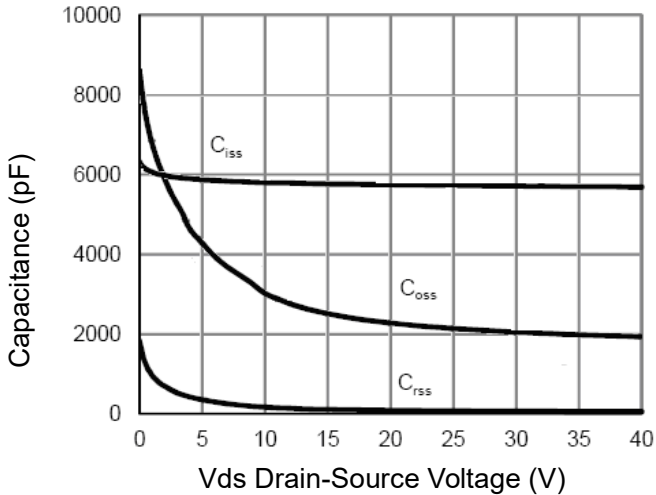
**Figure 4 Rdson-Junction Temperature**



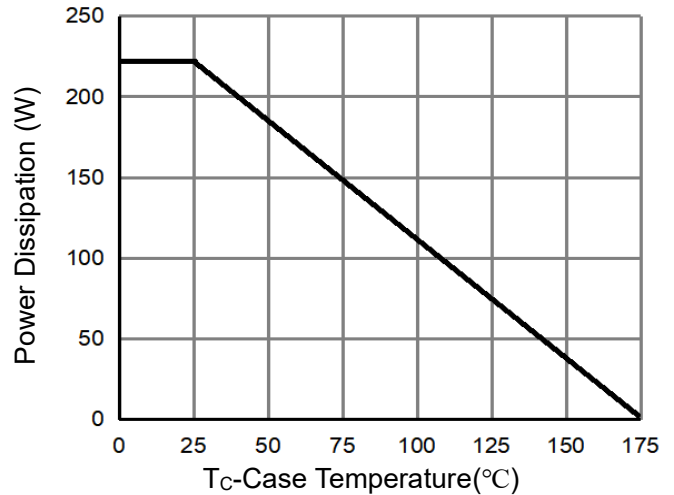
**Figure 5 Gate Charge**



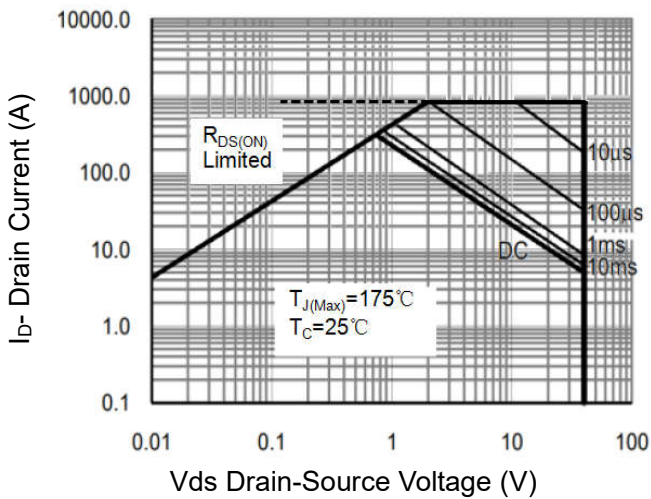
**Figure 6 Source- Drain Diode Forward**



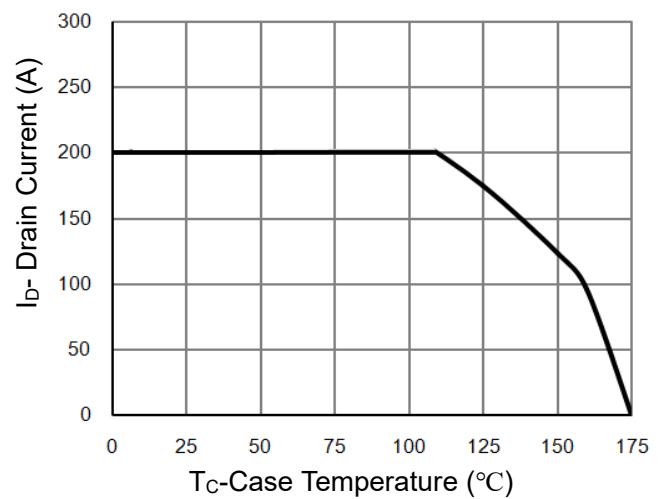
**Figure 7 Capacitance vs Vds**



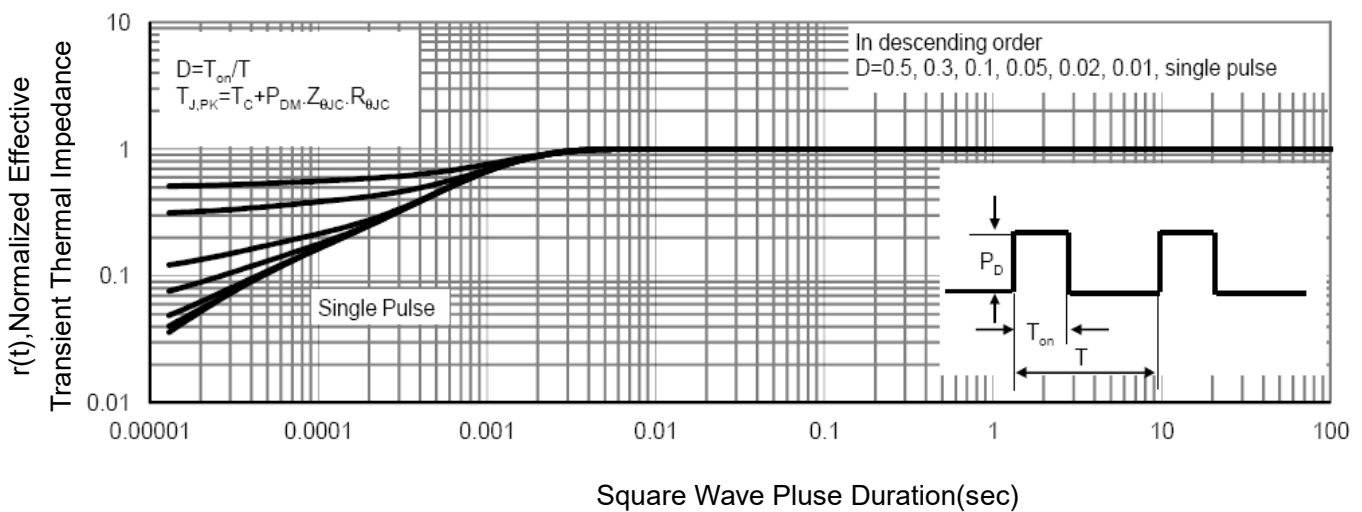
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area** (Note 3)

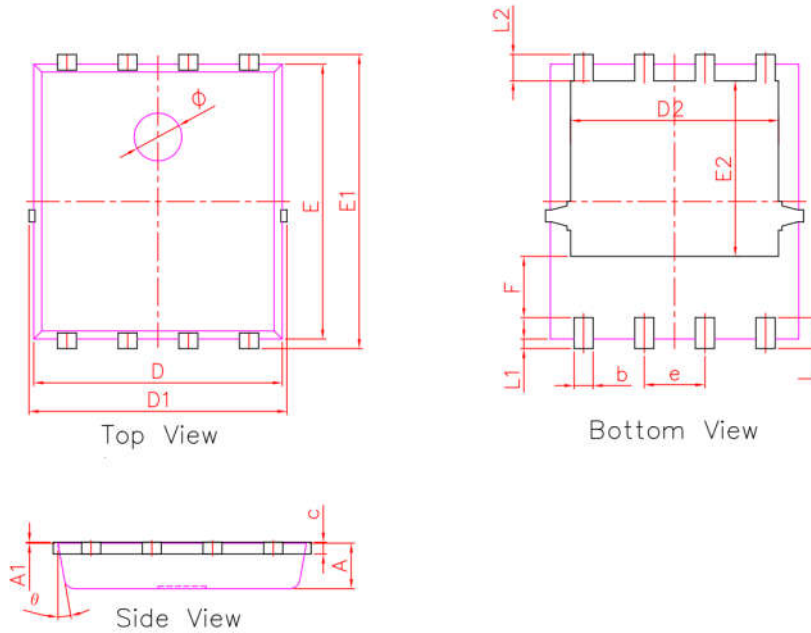


**Figure 10 Current De-rating**



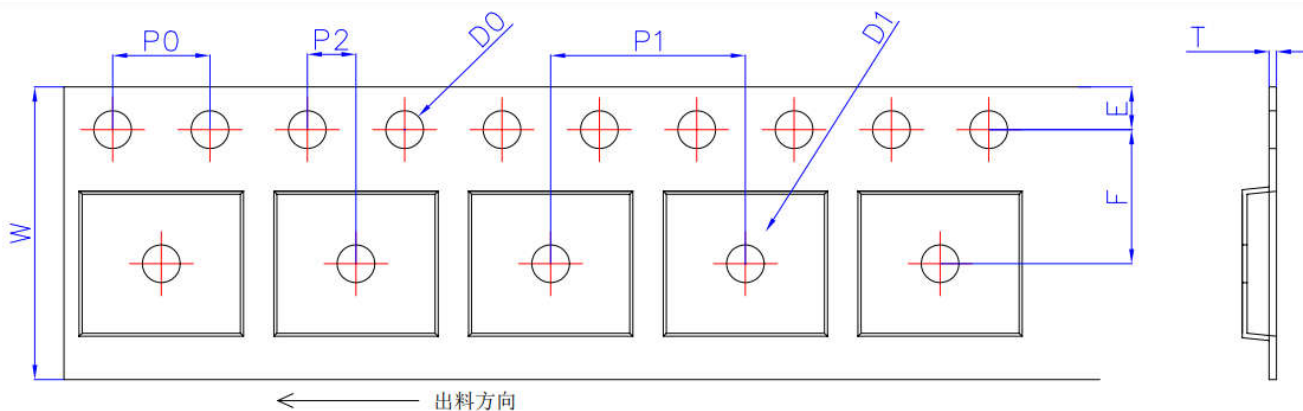
**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information

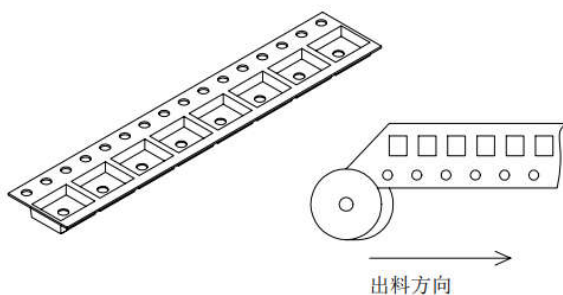


PDFN5X6-8L			
DIM.	MIN.	NOM.	MAX.
A	0.90	0.95	1.00
A1	0.00	0.02	0.05
b	0.35	0.40	0.50
c	0.20	0.25	0.30
D	5.10	5.20	5.30
D1	5.10	5.40	5.50
D2	4.25	4.35	4.45
e	1.27 BSC		
E	5.70	5.75	5.80
E1	6.00	6.15	6.30
E2	3.57	3.67	3.77
F	1.18	1.28	1.38
L	0.55	0.65	0.75
L1	0.15	0.20	0.25
L2	0.45	0.55	0.65
$\phi$	0.90	1.00	1.10
$\theta$	8°	10°	12°
All dimensions in millimeters			

## Tape And Reel Information

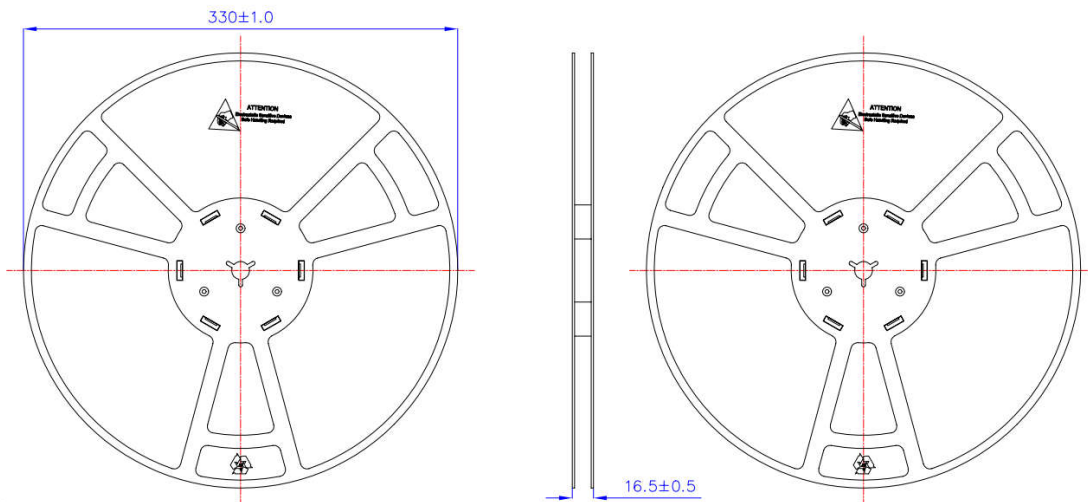


尺寸	W	T	D0	D1	
规格	12.00±0.1/+0.3	0.30±0.05	1.55±0.10	1.55±0.10	
尺寸	P0	P1	P2	E	F
规格	4.00±0.10	8.00±0.10	2.00±0.10	1.75±0.10	5.50±0.10



Note:

1. 累计公差：传送链孔10孔为 $40 \pm 0.20$
2. 未注R角，最大R0.3
3. 材质：PS BLACK
4. 电阻率： $10^{-5} \sim 10^{-11} \Omega / \text{cm}^2$



技术要求:

1. 材质：Hips
2. 颜色：蓝色
3. 电阻率： $10^{-6} \sim 10^{-11} \Omega / \text{SQ}$ ;

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